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DMN2055UWQ

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
20V	46mΩ @ V_{GS} = 4.5V	3.1A
	53mΩ @ V_{GS} = 2.5V	2.8A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN2055UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

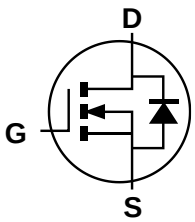
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (Approximate)

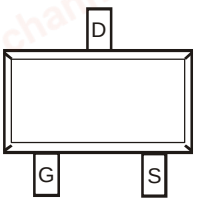
SOT323



Top View



Equivalent Circuit



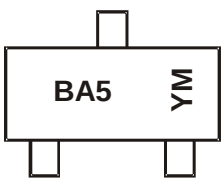
Top View
Pin-Out

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2055UWQ-7	SOT323	3,000/Tape & Reel
DMN2055UWQ-13	SOT323	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BA5 = Product Type Marking Code
YM or $\overline{Y}$M = Date Code Marking
Y or $\overline{Y}$ = Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	H	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C	I_D	3.1	A
		T_A = +70°C		2.4	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	22	A
Maximum Body Diode Forward Current (Note 5)			I_S	0.8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.52	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	241	°C/W
Total Power Dissipation (Note 6)		P_D	0.65	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	191	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current @T_C = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	35	46	mΩ	V_{GS} = 4.5V, I_D = 3.6A
		—	39	53		V_{GS} = 2.5V, I_D = 3.1A
Diode Forward Voltage	V_{SD}	—	0.7	1	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	400	—	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	55	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	37	—	pF	
Gate Resistance	R_g	—	3.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	4.3	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6A
Gate-Source Charge	Q_{gs}	—	0.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	4.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.8	—	ns	V_{DD} = 10V, V_{GS} = 5V, R_L = 1.7Ω, R_g = 6Ω
Turn-On Rise Time	t_R	—	2.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	15.4	—	ns	
Turn-Off Fall Time	t_F	—	4.4	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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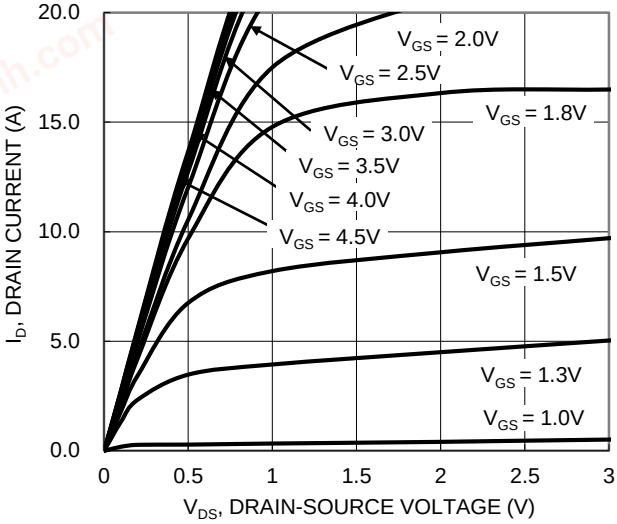


Figure 1. Typical Output Characteristic

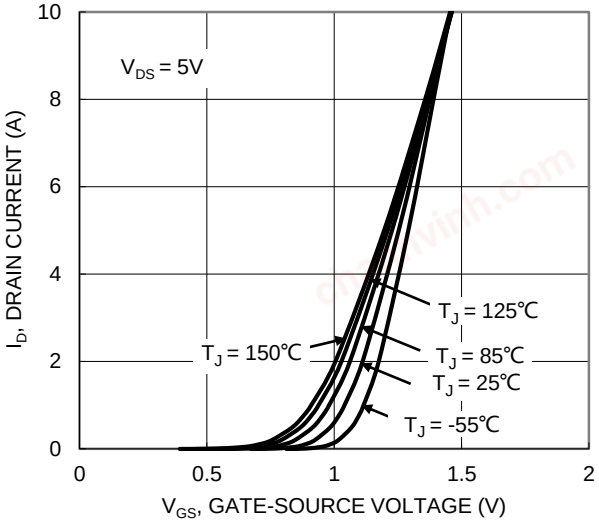


Figure 2. Typical Transfer Characteristic

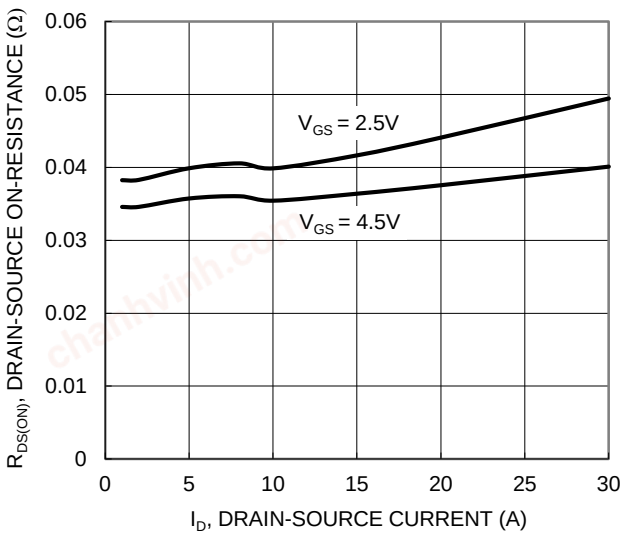


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

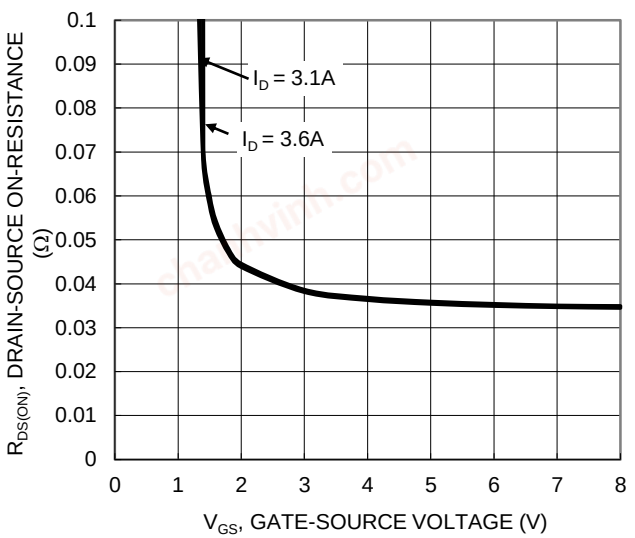


Figure 4. Typical Transfer Characteristic

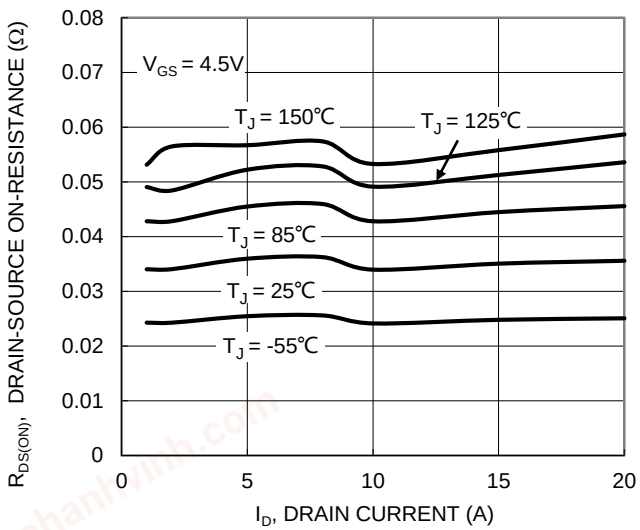


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

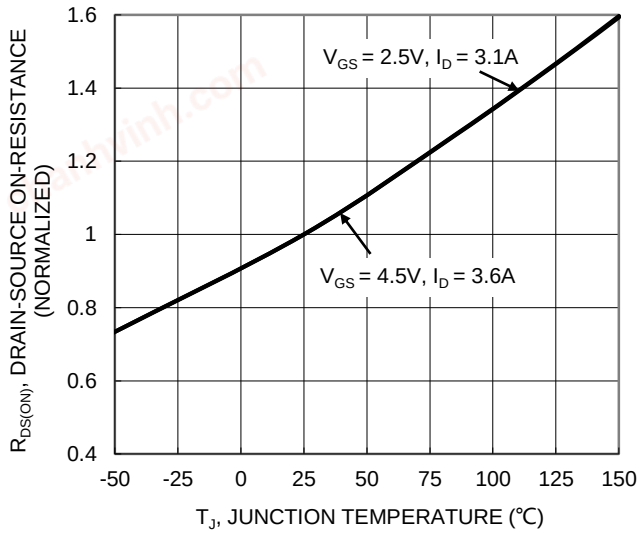


Figure 6. On-Resistance Variation with Junction Temperature

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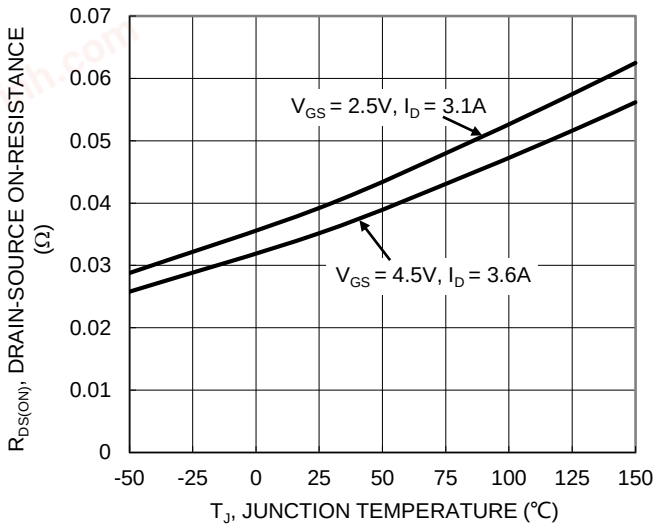


Figure 7. On-Resistance Variation with Junction Temperature

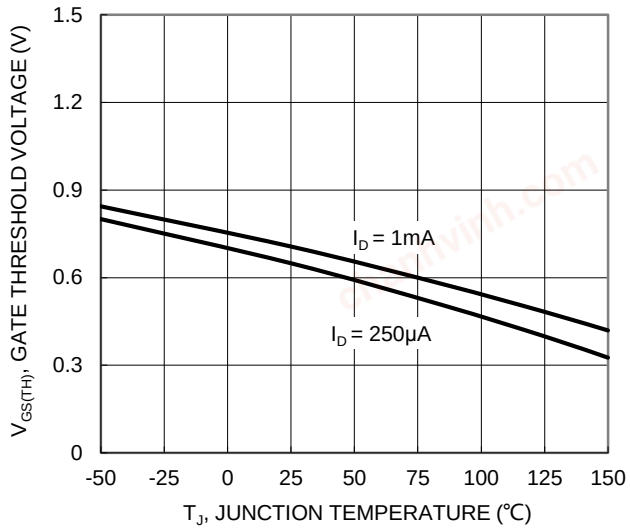


Figure 8. Gate Threshold Variation vs. Junction Temperature

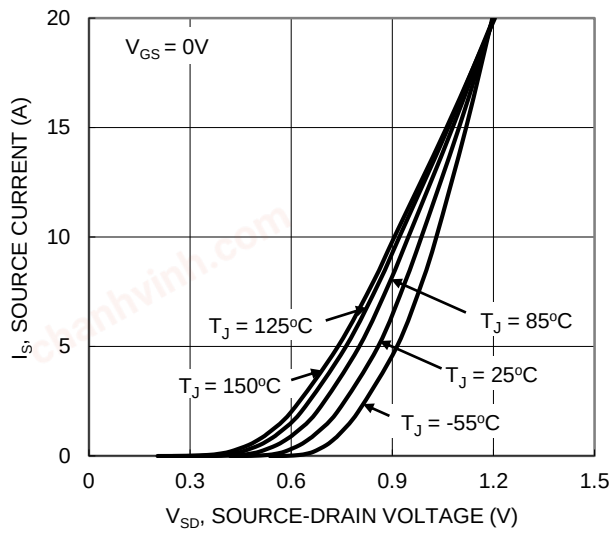


Figure 9. Diode Forward Voltage vs. Current

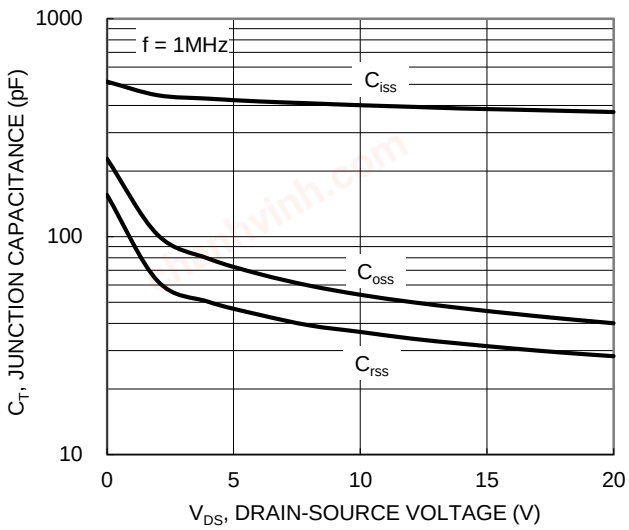


Figure 10. Typical Junction Capacitance

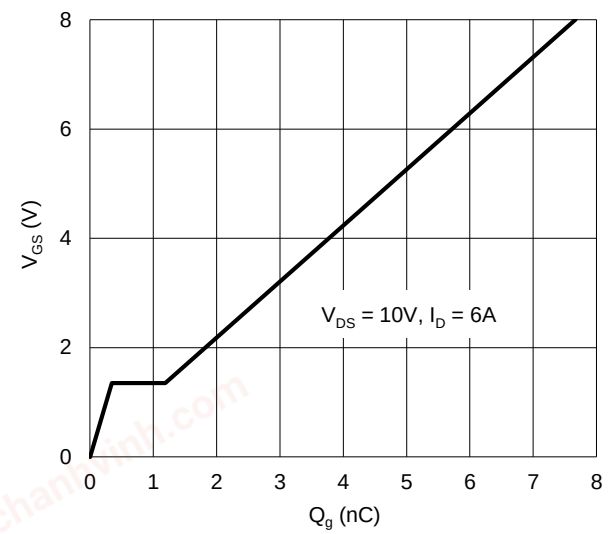


Figure 11. Gate Charge

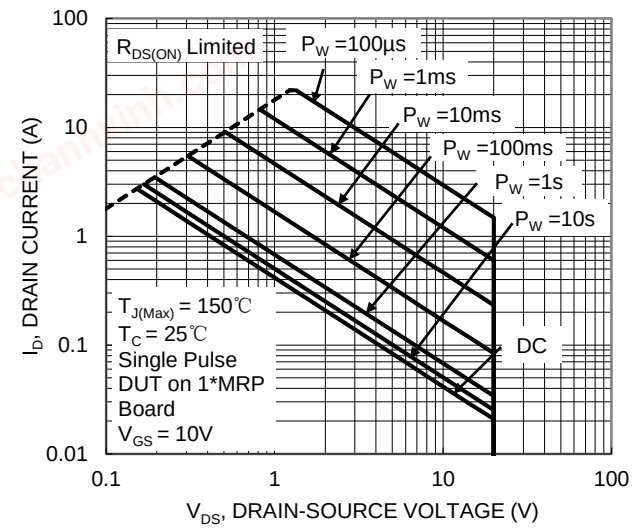


Figure 12. SOA, Safe Operation Area

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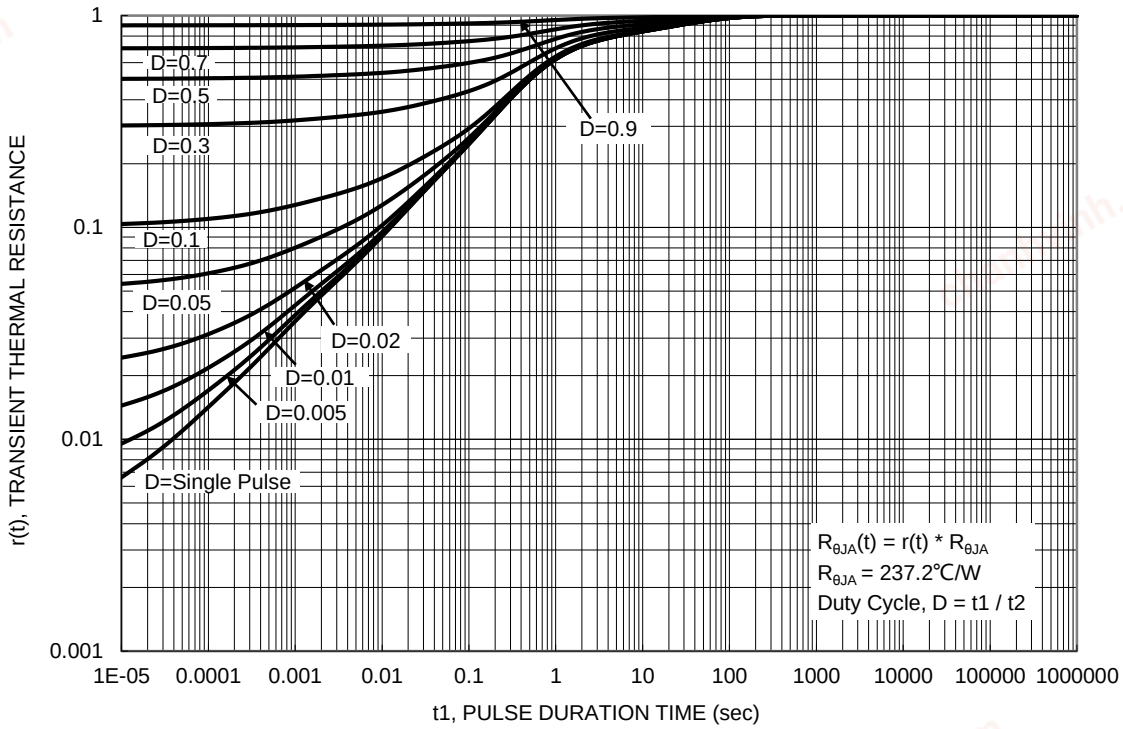


Figure 13. Transient Thermal Resistance

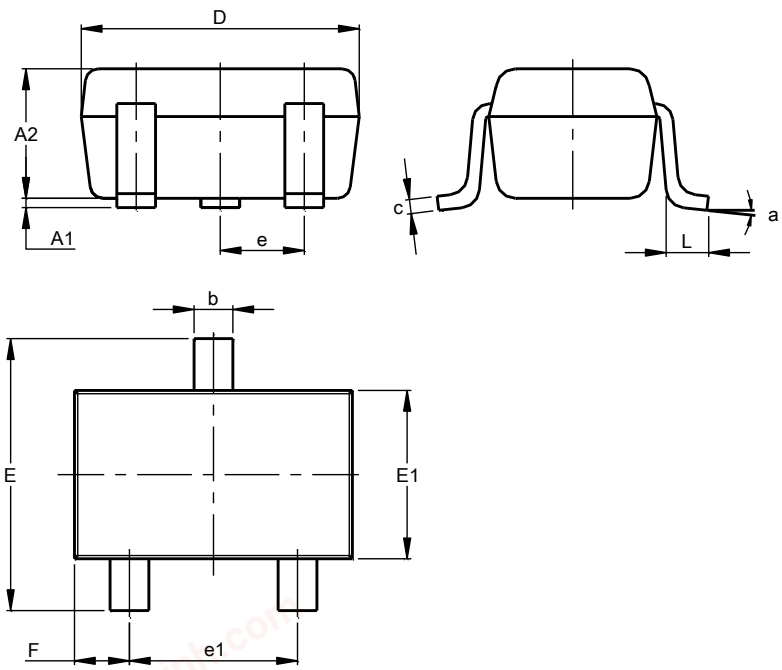
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

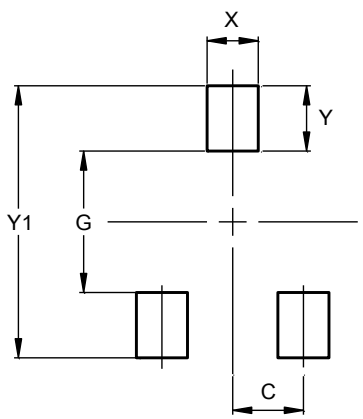


SOT323			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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